Siliconix

VN0610L, VN10KE/KM, VN2222L

N-Channel Enhancement-Mode MOS Transistors

Zener Gate Protected

Product Summary

Part Number	$V_{(BR)DSS}$ Min (V)	$r_{DS(on)}$ Max (Ω)	$V_{GS(th)}$ (V)	I_D (A)
VN0610L	60	5 @ V_{GS} = 10 V	0.8 to 2.5	0.27
VN10KE		5 @ V_{GS} = 10 V	0.8 to 2.5	0.17
VN10KM		5 @ V_{GS} = 10 V	0.8 to 2.5	0.31
VN2222L		7.5 @ V_{GS} = 10 V	0.6 to 2.5	0.23

Features

- Zener Diode Input Protected
- Low On-Resistance: 3 Ω
- Ultralow Threshold: 1.2 V
- Low Input Capacitance: 38 pF
- Low Input and Output Leakage

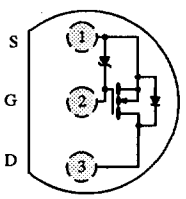
Benefits

- Extra ESD Protection
- Low Offset Voltage
- Low-Voltage Operation
- High-Speed, Easily Driven
- Low Error Voltage

Applications

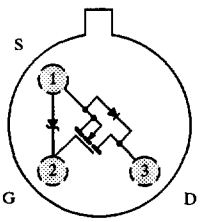
- Drivers: Relays, Solenoids, Lamps, Hammers, Displays, Memories, Transistors, etc.
- Battery Operated Systems
- Solid-State Relays
- Inductive Load Drivers

TO-226AA
(TO-92)



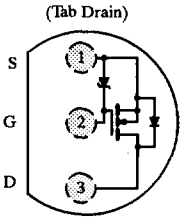
Top View
VN0610L
VN2222L

TO-206AC
(TO-52)



Top View
VN10KE

TO-237
(Tab Drain)



Top View
VN10KM

Absolute Maximum Ratings (T_A = 25°C Unless Otherwise Noted)

Parameter		Symbol	VN0610L	VN10KE	VN10KM	VN2222L	Unit
Drain-Source Voltage		V_{DS}	60	60	60	60	V
Gate-Source Voltage		V_{GS}	15/−0.3	15/−0.3	15/−0.3	15/−0.3	
Continuous Drain Current (T_J = 150°C)	T_A = 25°C	I_D	0.27	0.17	0.31	0.23	A
	T_A = 100°C		0.17	0.11	0.20	0.14	
Pulsed Drain Current[a]		I_{DM}	1	1	1	1	
Power Dissipation	T_A = 25°C	P_D	0.8	0.3	1	0.8	W
	T_A = 100°C		0.32	0.12	0.4	0.32	
Maximum Junction-to-Ambient		R_{thJA}	156	400	125	156	°C/W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	−55 to 150				°C

Notes
a. Pulse width limited by maximum junction temperature.

VN0610L, VN10KE/KM, VN2222L

Specifications[a]

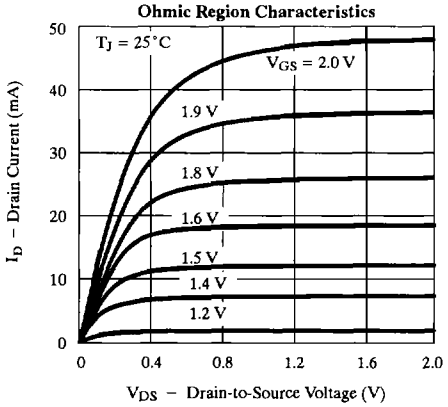
Parameter	Symbol	Test Conditions	Typ[b]	Limits VN0610L VN10KE VN10KM Min	Limits VN0610L VN10KE VN10KM Max	Limits VN2222L Min	Limits VN2222L Max	Unit
Static								
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 100 µA	120	60		60		V
Gate-Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 1 mA	1.2	0.8	2.5	0.6	2.5	V
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = 15 V	1		100		100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 48 V, V_{GS} = 0 V			10		10	µA
		T_J = 125°C			500		500	µA
On-State Drain Current[c]	$I_{D(on)}$	V_{DS} = 10 V, V_{GS} = 10 V	1	0.75		0.75		A
Drain-Source On-Resistance[c]	$r_{DS(on)}$	V_{GS} = 5 V, I_D = 0.2 A	4		7.5		7.5	Ω
		V_{GS} = 10 V, I_D = 0.5 A	3		5		7.5	Ω
		T_J = 125°C	5.6		9		13.5	Ω
Forward Transconductance[c]	g_{fs}	V_{DS} = 10 V, I_D = 0.5 A	300	100		100		mS
Common Source Output Conductance[c]	g_{os}	V_{DS} = 7.5 V, I_D = 0.05 A	0.2					mS
Dynamic								
Input Capacitance	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz	38		60		60	pF
Output Capacitance	C_{oss}		16		25		25	pF
Reverse Transfer Capacitance	C_{rss}		2		5		5	pF
Switching[d]								
Turn-On Time	t_{ON}	V_{DD} = 15 V, R_L = 23 Ω, I_D ≅ 0.6 A, V_{GEN} = 10 V, R_G ≈ 25 Ω	7		10		10	ns
Turn-Off Time	t_{OFF}		9		10		10	ns

Notes
a. T_A = 25°C unless otherwise noted.
b. For DESIGN AID ONLY, not subject to production testing.
c. Pulse test: PW ≤ 300 µs duty cycle ≤ 2%.
d. Switching time is essentially independent of operating temperature.

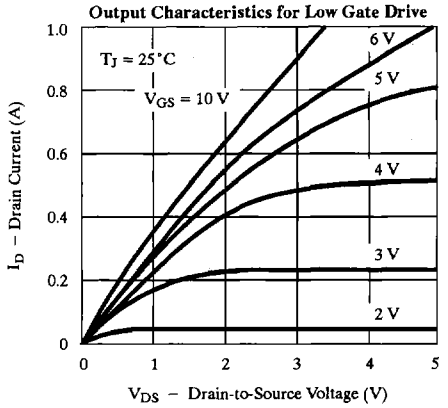
VNDP06

Typical Characteristics (25°C Unless Otherwise Noted)

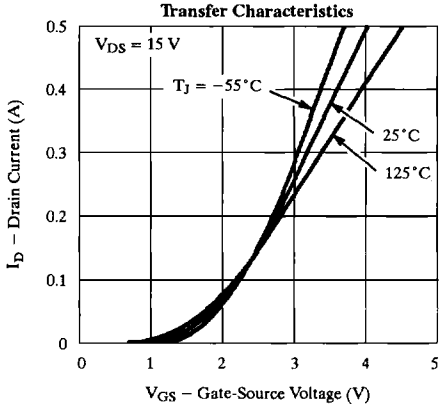
Ohmic Region Characteristics



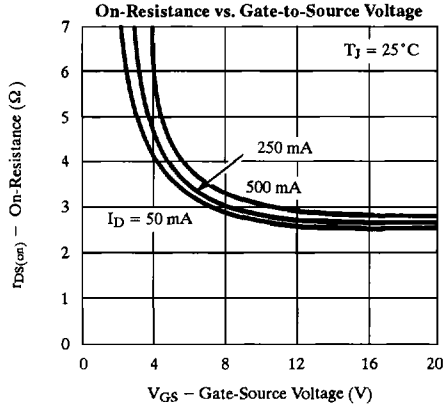
Output Characteristics for Low Gate Drive



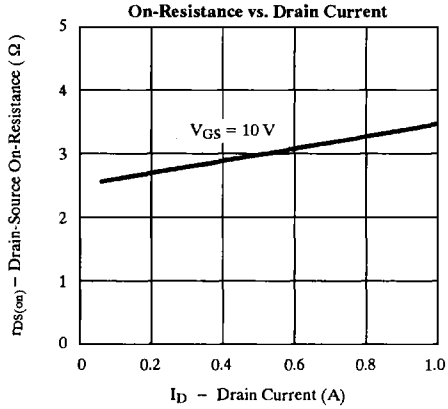
Transfer Characteristics



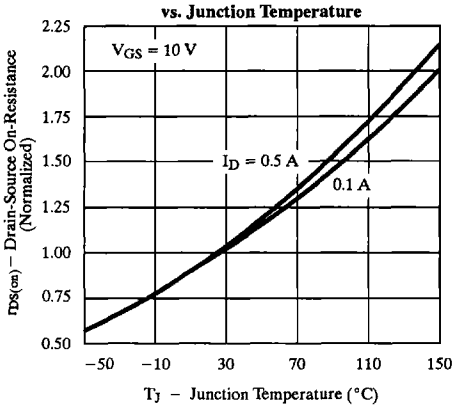
On-Resistance vs. Gate-to-Source Voltage



On-Resistance vs. Drain Current



Normalized On-Resistance vs. Junction Temperature



Typical Characteristics (25°C Unless Otherwise Noted) (Cont'd)